

**METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING A
LOW K DIELECTRIC**

Abstract of the Disclosure

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A low K dielectric layer and a cap for the low K dielectric layer are formed in situ using the same silicon precursors but at different precursor ratios. The low K dielectric is deposited with precursors that are useful for making a low K dielectric. Trenches are formed in the low K dielectric and are filled by a
10 metal layer. Chemical mechanical processing (CMP) is utilized to remove the metal outside the trench while the cap aids planarity outside the trench.